

IS61LV256AL

32K x 8 LOW VOLTAGE CMOS STATIC RAM

AUGUST 2009

FEATURES

- High-speed access times:
 - 10 ns
- Automatic power-down when chip is deselected
- CMOS low power operation
 - 60 μ W (typical) CMOS standby
 - 65 mW (typical) operating
- TTL compatible interface levels
- Single 3.3V power supply
- Fully static operation: no clock or refresh required
- Three-state outputs
- Lead-free available

DESCRIPTION

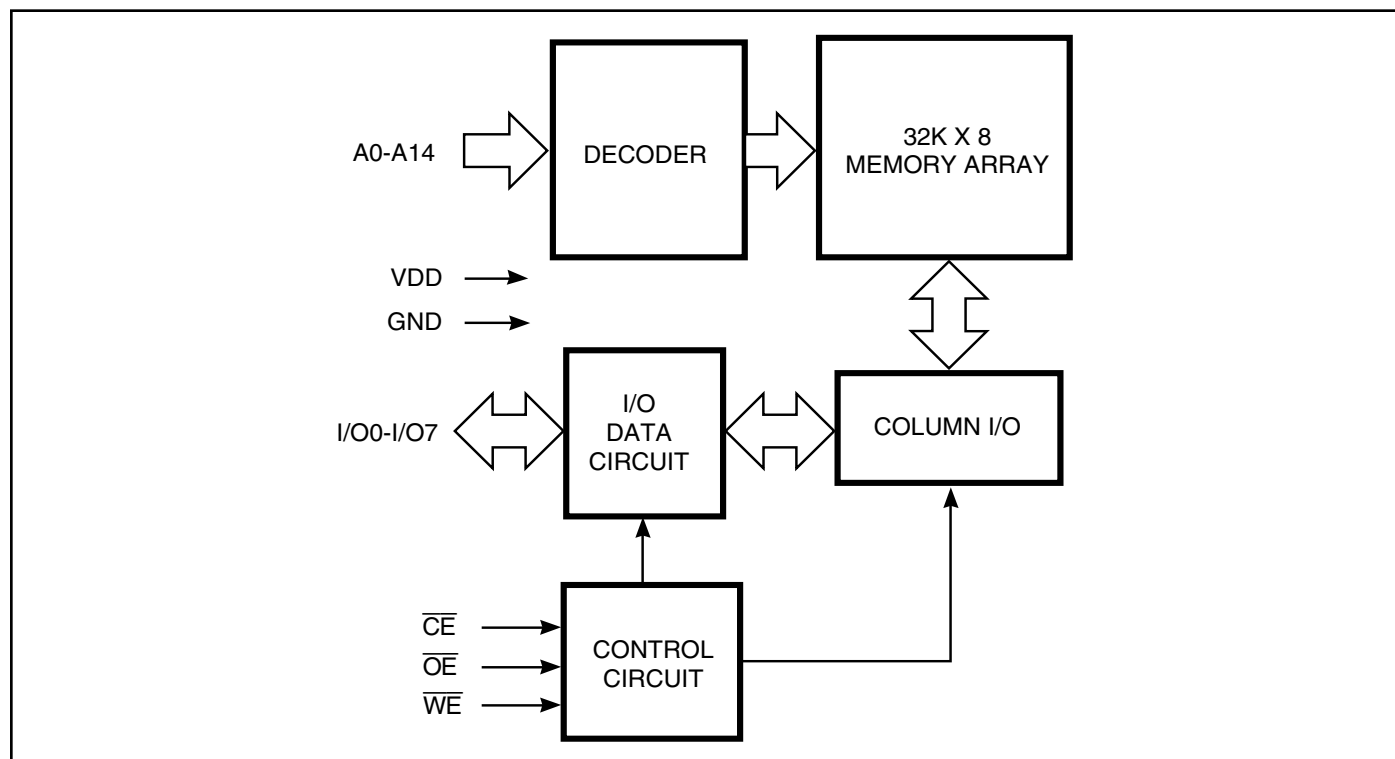
The *ISSI* IS61LV256AL is a very high-speed, low power, 32,768-word by 8-bit static RAM. It is fabricated using *ISSI*'s high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields access times as fast as 8 ns maximum.

When \overline{CE} is HIGH (deselected), the device assumes a standby mode at which the power dissipation is reduced to 150 μ W (typical) with CMOS input levels.

Easy memory expansion is provided by using an active LOW Chip Enable (\overline{CE}). The active LOW Write Enable (\overline{WE}) controls both writing and reading of the memory.

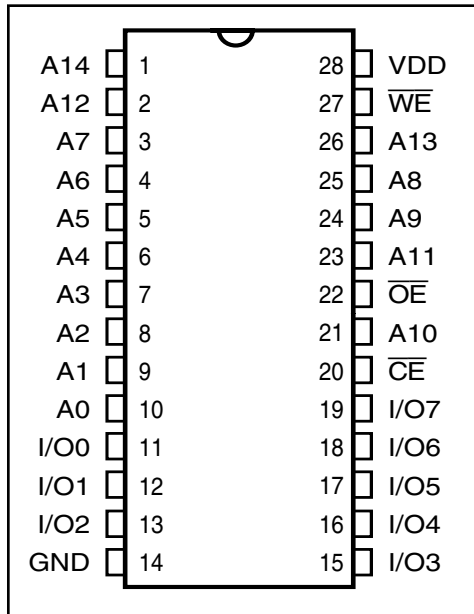
The IS61LV256AL is available in the JEDEC standard 28-pin, 300-mil SOJ and the 450-mil TSOP (Type I) packages.

FUNCTIONAL BLOCK DIAGRAM



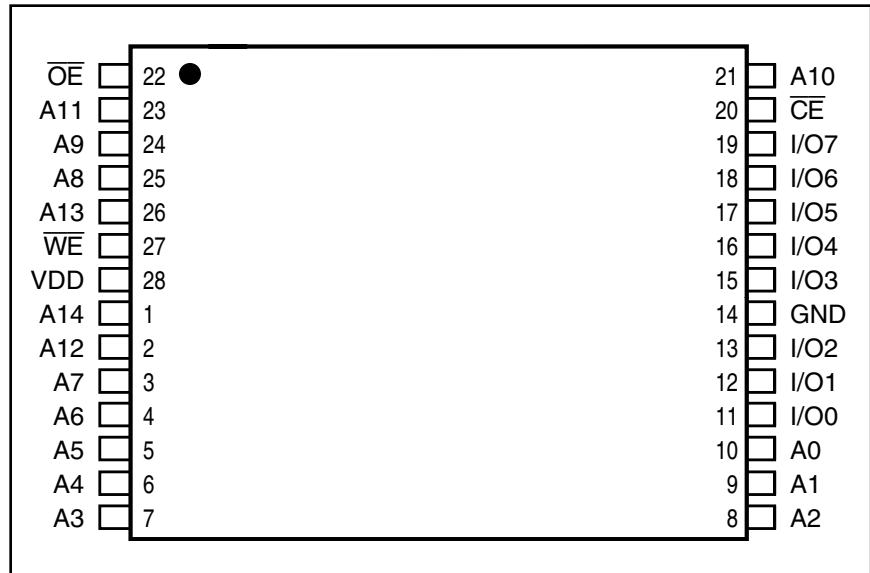
PIN CONFIGURATION

28-Pin SOJ



PIN CONFIGURATION

28-Pin TSOP (Type I)



PIN DESCRIPTIONS

| | |
|-----------------|---------------------|
| A0-A14 | Address Inputs |
| \overline{CE} | Chip Enable Input |
| \overline{OE} | Output Enable Input |
| \overline{WE} | Write Enable Input |
| I/O0-I/O7 | Input/Output |
| V _{DD} | Power |
| GND | Ground |

TRUTH TABLE

| Mode | \overline{WE} | \overline{CE} | \overline{OE} | I/O Operation | V _{DD} Current |
|------------------------------|-----------------|-----------------|-----------------|------------------|-------------------------------------|
| Not Selected (Power-down) | X | H | X | High-Z | I _{SB1} , I _{SB2} |
| Output Disabled | H | L | H | High-Z | I _{CC} |
| Read | H | L | L | D _{OUT} | I _{CC} |
| Write | L | L | X | D _{IN} | I _{CC} |

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

| Symbol | Parameter | Value | Unit |
|-------------------|--------------------------------------|--------------|------|
| V _{DD} | Power Supply Voltage Relative to GND | -0.5 to +4.6 | V |
| V _{TERM} | Terminal Voltage with Respect to GND | -0.5 to +4.6 | V |
| T _{STG} | Storage Temperature | -65 to +150 | °C |
| P _D | Power Dissipation | 1 | W |
| I _{OUT} | DC Output Current | ±20 | mA |

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

OPERATING RANGE

| Range | Ambient Temperature | Speed (ns) | V _{DD} ⁽¹⁾ |
|------------|---------------------|------------|--------------------------------|
| Commercial | 0°C to +70°C | 10 | 3.3V, +10%, -5% |
| Industrial | -40°C to +85°C | 10 | 3.3V + 10%, -5% |

Note: 1. If operated at 12ns, V_{DD} range is 3.3V ± 10%.

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

| Symbol | Parameter | Test Conditions | Min. | Max. | Unit | |
|-----------------|----------------------------------|---|------|-----------------------|------|----|
| V _{OH} | Output HIGH Voltage | V _{DD} = Min., I _{OH} = -2.0 mA | 2.4 | — | V | |
| V _{OL} | Output LOW Voltage | V _{DD} = Min., I _{OL} = 4.0 mA | — | 0.4 | V | |
| V _{IH} | Input HIGH Voltage | | 2.2 | V _{DD} + 0.3 | V | |
| V _{IL} | Input LOW Voltage ⁽¹⁾ | | -0.3 | 0.8 | V | |
| I _{LI} | Input Leakage | GND ≤ V _{IN} ≤ V _{DD} | Com. | -1 | 1 | μA |
| | | | Ind. | -2 | 2 | |
| I _{LO} | Output Leakage | GND ≤ V _{OUT} ≤ V _{DD} , Outputs Disabled | Com. | -1 | 1 | μA |
| | | | Ind. | -2 | 2 | |

Notes:

- V_{IL} (min.) = -0.3V (DC); V_{IL} (min.) = -2.0V (pulse width ≤ 2.0 ns).
V_{IH} (max.) = V_{DD} + 0.5V (DC); V_{IH} (max.) = V_{DD} + 2.0V (pulse width ≤ 2.0 ns).
- Not more than one output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.

POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

| Sym. | Parameter | Test Conditions | | -10 ns | | Unit |
|------------------|--|---|---------------------|--------|------|---------|
| | | | | Min. | Max. | |
| I _{CC1} | V _{DD} Operating Supply Current | V _{DD} = Max., \overline{CE} = V _{IL} I _{OUT} = 0 mA, f = 1 MHz | Com. | — | 20 | mA |
| | | | Ind. | — | 25 | |
| I _{CC2} | V _{DD} Dynamic Operating Supply Current | V _{DD} = Max., \overline{CE} = V _{IL} I _{OUT} = 0 mA, f = f _{MAX} | Com. | — | 30 | mA |
| | | | Ind. | — | 35 | |
| | | | typ. ⁽²⁾ | | 20 | |
| I _{SB1} | TTL Standby Current (TTL Inputs) | V _{DD} = Max., V _{IN} = V _{IH} or V _{IL} $\overline{CE} \geq V_{IH}$, f = 0 | Com. | — | 1 | mA |
| | | | Ind. | — | 1 | |
| I _{SB2} | CMOS Standby Current (CMOS Inputs) | V _{DD} = Max., $\overline{CE} \geq V_{DD} - 0.2V$, V _{IN} $\geq V_{DD} - 0.2V$, or V _{IN} $\leq 0.2V$, f = 0 | Com. | — | 40 | μ A |
| | | | Ind. | — | 50 | |
| | | | typ. ⁽²⁾ | | 2 | |

Notes:

- At f = f_{MAX}, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.
- Typical values are measured at V_{DD} = 3.3V, T_A = 25°C and not 100% tested.

CAPACITANCE^(1,2)

| Symbol | Parameter | Conditions | Max. | Unit |
|------------------|--------------------|-----------------------|------|------|
| C _{IN} | Input Capacitance | V _{IN} = 0V | 6 | pF |
| C _{OUT} | Output Capacitance | V _{OUT} = 0V | 5 | pF |

Notes:

- Tested initially and after any design or process changes that may affect these parameters.
- Test conditions: T_A = 25°C, f = 1 MHz, V_{DD} = 3.3V.

READ CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

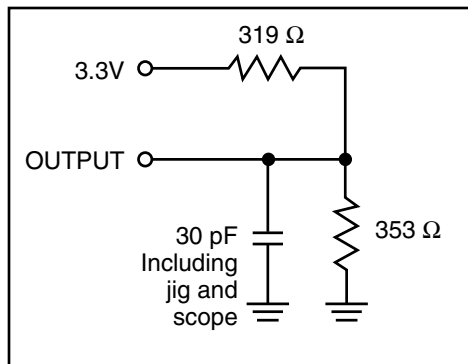
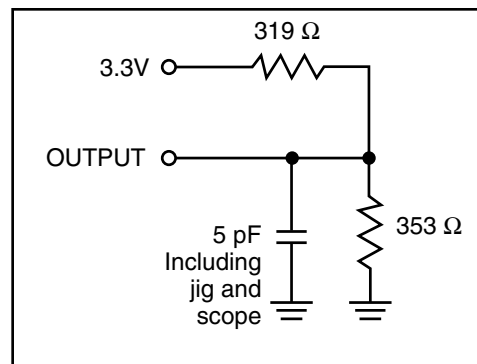
| Symbol | Parameter | -10 ns | | -12 ns | | Unit |
|----------------------------------|----------------------------------|--------|------|--------|------|------|
| | | Min. | Max. | Min. | Max. | |
| t _{RC} | Read Cycle Time | 10 | — | 12 | — | ns |
| t _{AA} | Address Access Time | — | 10 | — | 12 | ns |
| t _{OHA} | Output Hold Time | 2 | — | 2 | — | ns |
| t _{ACE} | \overline{CE} Access Time | — | 10 | — | 12 | ns |
| t _{DOE} | \overline{OE} Access Time | — | 5 | — | 5 | ns |
| t _{LZOE} ⁽²⁾ | \overline{OE} to Low-Z Output | 0 | — | 0 | — | ns |
| t _{HZOE} ⁽²⁾ | \overline{OE} to High-Z Output | — | 5 | — | 5 | ns |
| t _{LZCE} ⁽²⁾ | \overline{CE} to Low-Z Output | 3 | — | 3 | — | ns |
| t _{HZCE} ⁽²⁾ | \overline{CE} to High-Z Output | — | 5 | — | 6 | ns |
| t _{PU} ⁽³⁾ | \overline{CE} to Power-Up | 0 | — | 0 | — | ns |
| t _{PD} ⁽³⁾ | \overline{CE} to Power-Down | — | 10 | — | 12 | ns |

Notes:

1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1.
2. Tested with the load in Figure 2. Transition is measured ± 200 mV from steady-state voltage. Not 100% tested.
3. Not 100% tested.

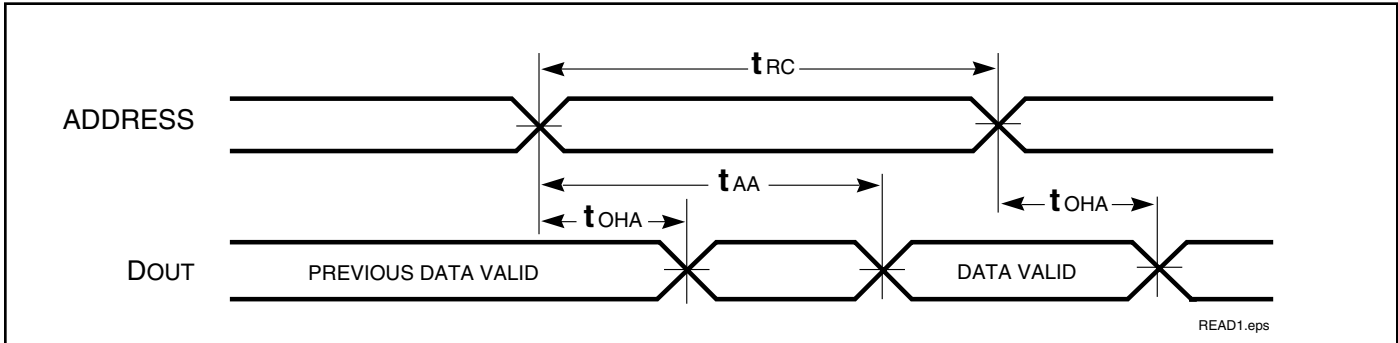
AC TEST CONDITIONS

| Parameter | Unit |
|--|---------------------|
| Input Pulse Level | 0V to 3.0V |
| Input Rise and Fall Times | 3 ns |
| Input and Output Timing and Reference Levels | 1.5V |
| Output Load | See Figures 1 and 2 |

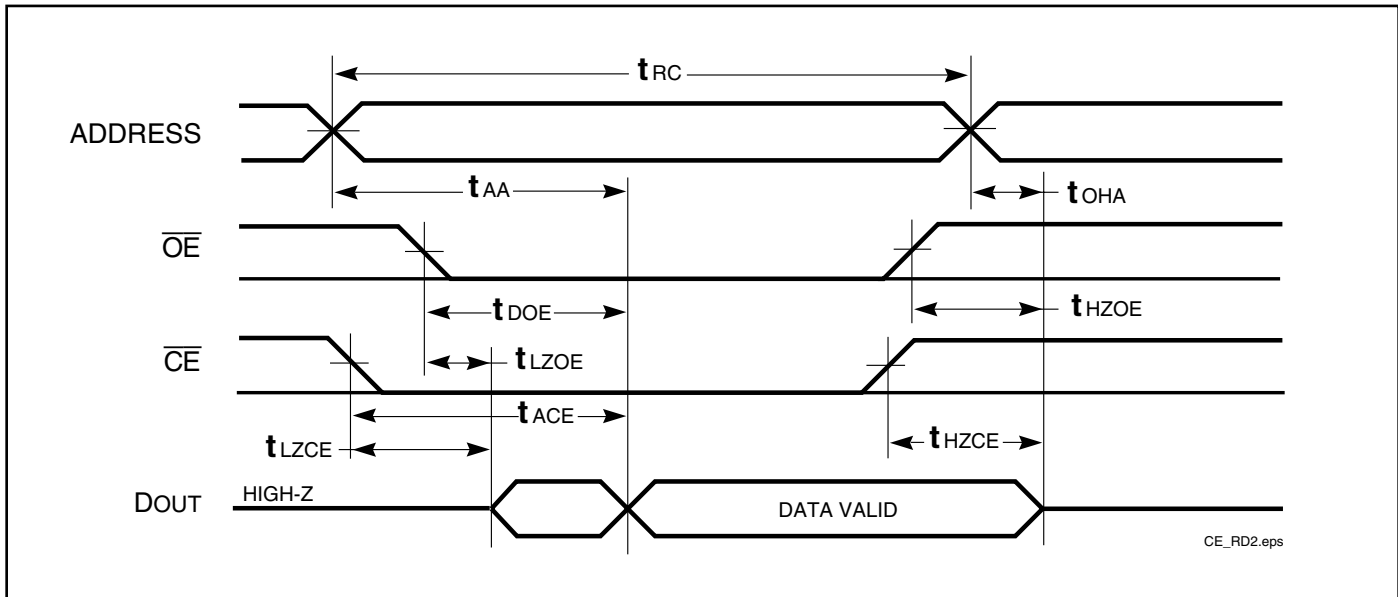
AC TEST LOADS

Figure 1.

Figure 2.

AC WAVEFORMS

READ CYCLE NO. 1^(1,2)



READ CYCLE NO. 2^(1,3)



Notes:

1. \overline{WE} is HIGH for a Read Cycle.
2. The device is continuously selected. \overline{OE} , \overline{CE} = V_{IL} .
3. Address is valid prior to or coincident with \overline{CE} LOW transitions.

WRITE CYCLE SWITCHING CHARACTERISTICS^(1,2) (Over Operating Range)

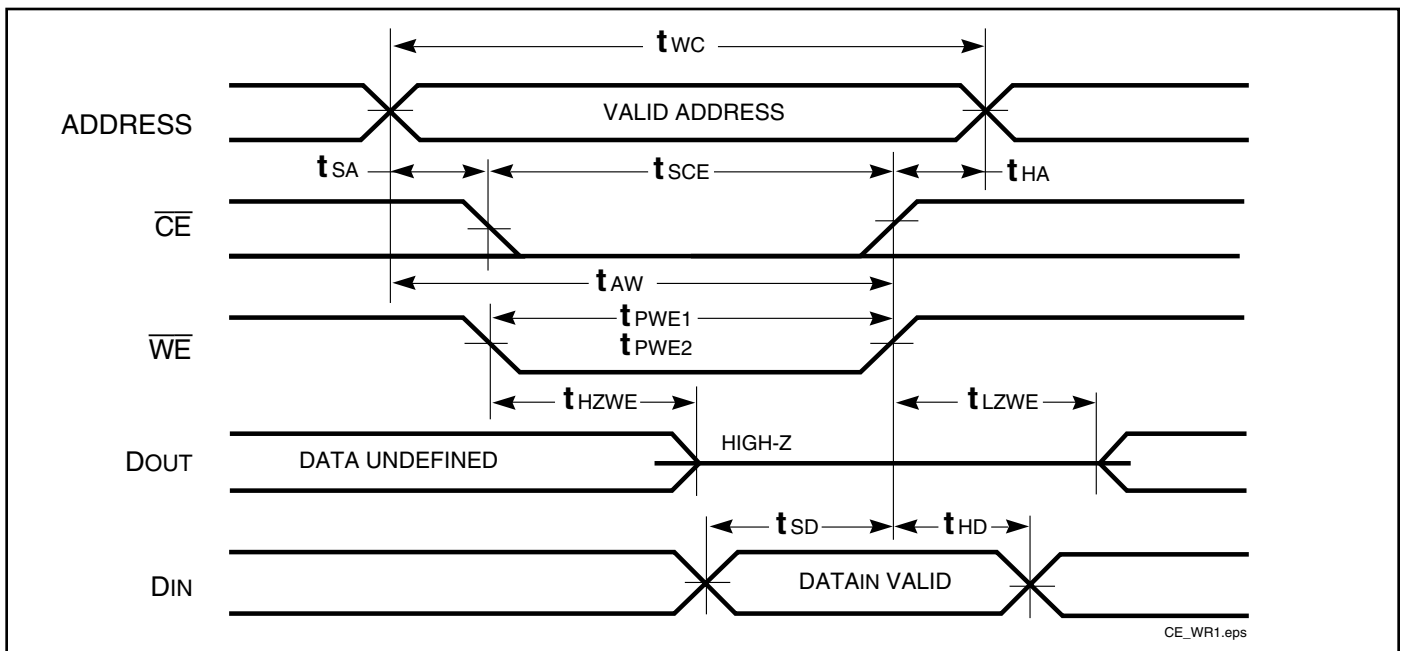
| Symbol | Parameter | -10 ns | | -12 ns | | Unit |
|----------------------------------|---|--------|------|--------|------|------|
| | | Min. | Max. | Min. | Max. | |
| t _{WC} | Write Cycle Time | 10 | — | 12 | — | ns |
| t _{SCE} | \overline{CE} to Write End | 8 | — | 8 | — | ns |
| t _{AW} | Address Setup Time to Write End | 8 | — | 8 | — | ns |
| t _{HA} | Address Hold from Write End | 0 | — | 0 | — | ns |
| t _{SA} | Address Setup Time | 0 | — | 0 | — | ns |
| t _{PWE1} | \overline{WE} Pulse Width (\overline{OE} HIGH) | 7 | — | 8 | — | ns |
| t _{PWE2} | \overline{WE} Pulse Width (\overline{OE} LOW) | 10 | — | 12 | — | ns |
| t _{SD} | Data Setup to Write End | 6.5 | — | 7 | — | ns |
| t _{HD} | Data Hold from Write End | 0 | — | 0 | — | ns |
| t _{HZWE} ⁽³⁾ | \overline{WE} LOW to High-Z Output | — | 3.5 | — | 5 | ns |
| t _{LZWE} ⁽³⁾ | \overline{WE} HIGH to Low-Z Output | 0 | — | 0 | — | ns |

Notes:

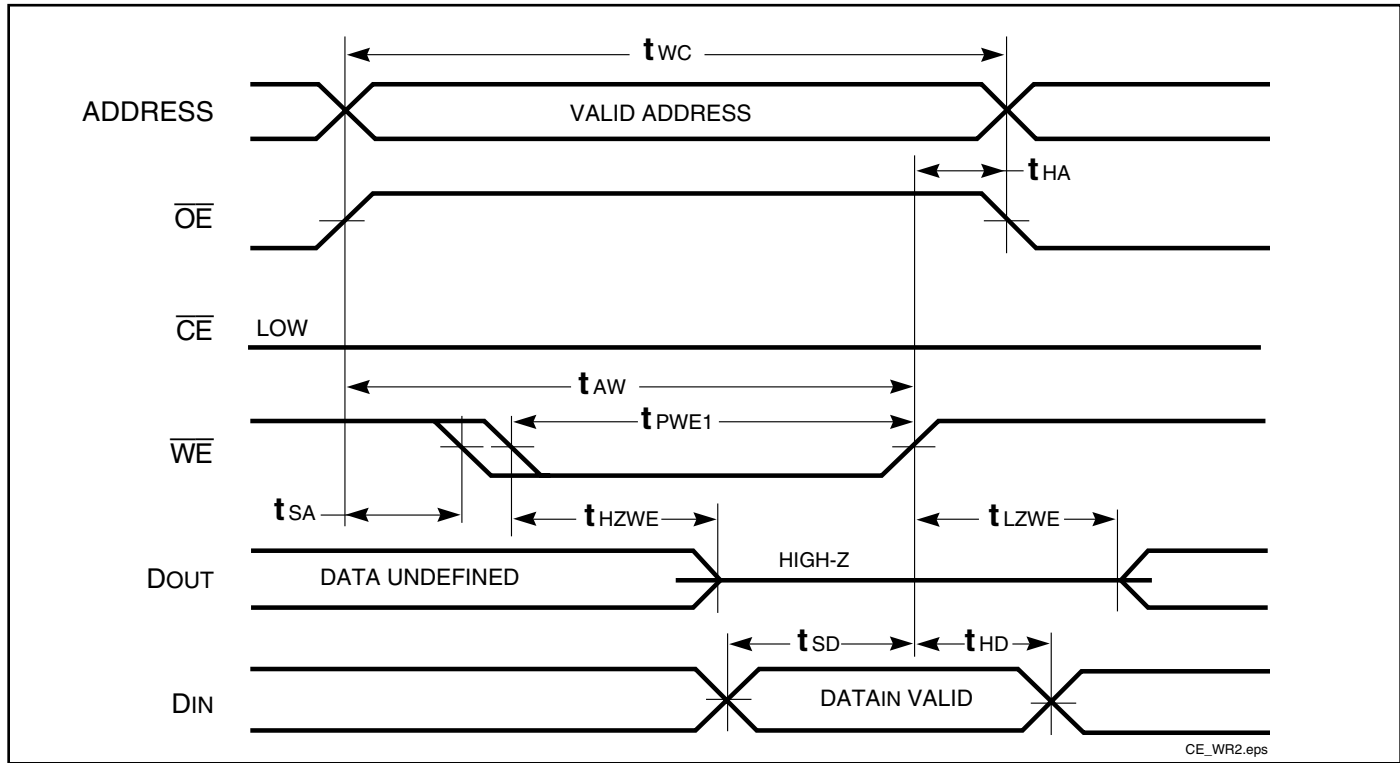
1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V and output loading specified in Figure 1.
2. The internal write time is defined by the overlap of \overline{CE} LOW and \overline{WE} LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the Write.
3. Tested with the load in Figure 2. Transition is measured ± 500 mV from steady-state voltage. Not 100% tested.

AC WAVEFORMS

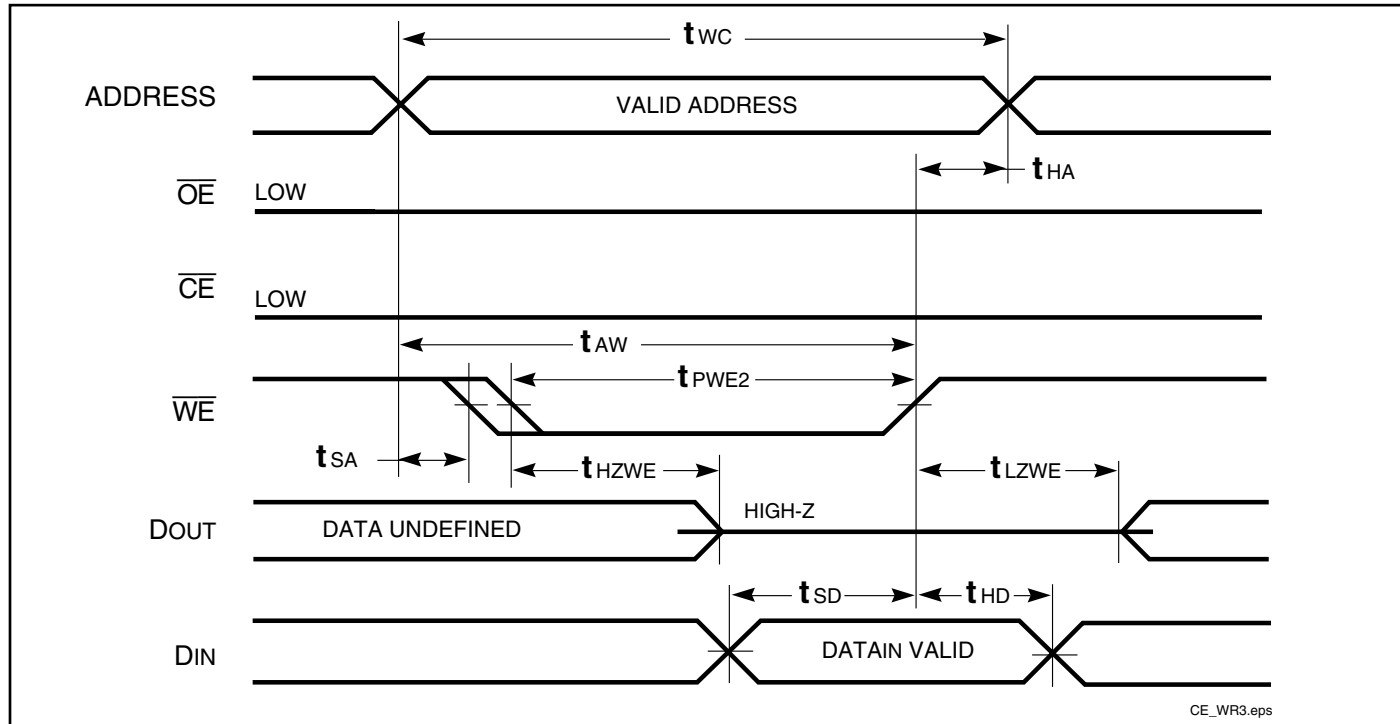
WRITE CYCLE NO. 1 (\overline{CE} Controlled, \overline{OE} is HIGH or LOW) ⁽¹⁾



WRITE CYCLE NO. 2 (\overline{WE} Controlled, \overline{OE} is HIGH During Write Cycle) ^(1,2)



WRITE CYCLE NO. 3 (\overline{WE} Controlled, \overline{OE} is LOW During Write Cycle) ⁽¹⁾



Notes:

1. The internal write time is defined by the overlap of \overline{CE} LOW and \overline{WE} LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the Write.
2. I/O will assume the High-Z state if $\overline{OE} > V_{IH}$.

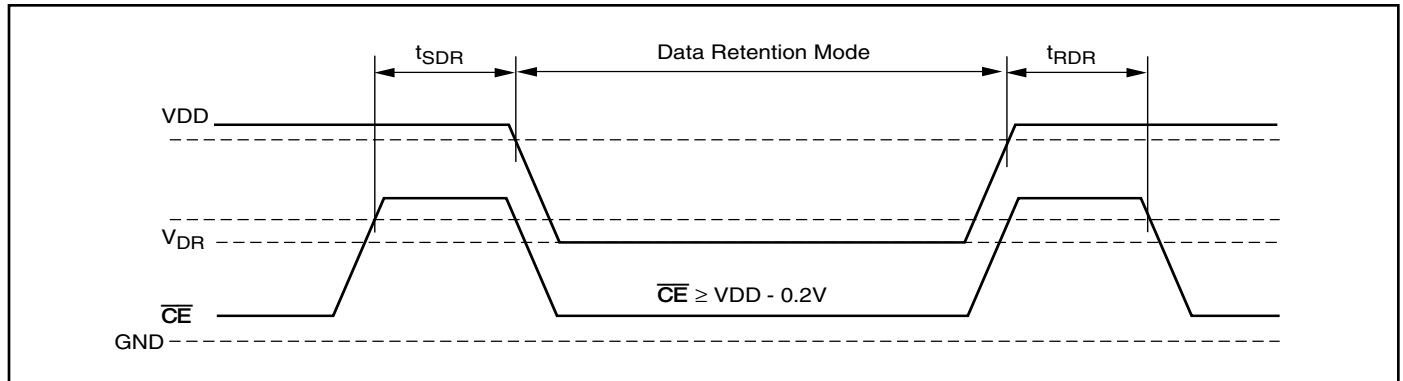
DATA RETENTION SWITCHING CHARACTERISTICS

| Symbol | Parameter | Test Condition | Min. | Typ. ⁽¹⁾ | Max. | Unit |
|------------------|------------------------------------|---|-----------------|---------------------|------|------|
| V _{DR} | V _{DD} for Data Retention | See Data Retention Waveform | 2.0 | | 3.6 | V |
| I _{DR} | Data Retention Current | V _{DD} = 2.0V, $\overline{CE} \geq V_{DD} - 0.2V$ V _{IN} ≥ V _{DD} - 0.2V, or V _{IN} ≤ V _{SS} + 0.2V | — | 2 | 40 | μA |
| t _{SDR} | Data Retention Setup Time | See Data Retention Waveform | 0 | | — | ns |
| t _{RDR} | Recovery Time | See Data Retention Waveform | t _{RC} | | — | ns |

Note:

1. Typical Values are measured at V_{DD} = 3.3V, T_A = 25°C and not 100% tested.

DATA RETENTION WAVEFORM (\overline{CE} Controlled)

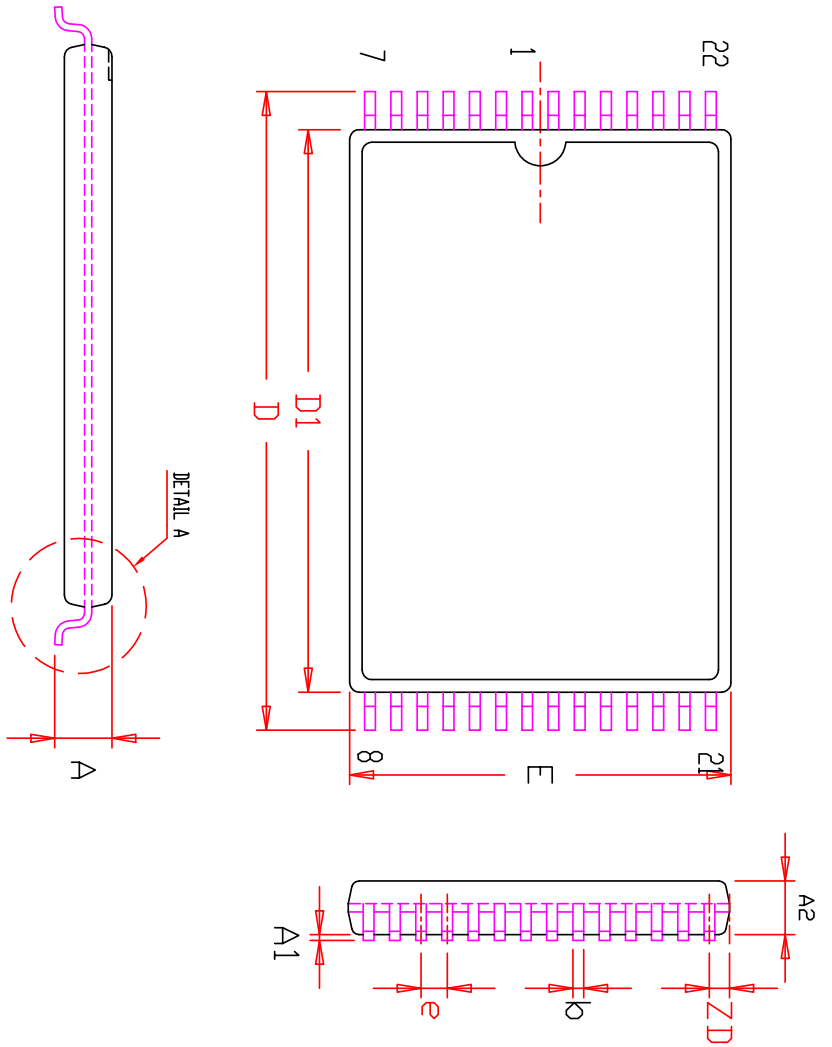


ORDERING INFORMATION**Commercial Range: 0°C to +70°C**

| Speed (ns) | Order Part No. | Package |
|------------|------------------|--------------------------------|
| 10 | IS61LV256AL-10T | TSOP - Type I |
| | IS61LV256AL-10TL | TSOP - Type I, Lead-free |
| | IS61LV256AL-10J | 300-mil Plastic SOJ |
| | IS61LV256AL-10JL | 300-mil Plastic SOJ, Lead-free |

ORDERING INFORMATION**Industrial Range: -40°C to +85°C**

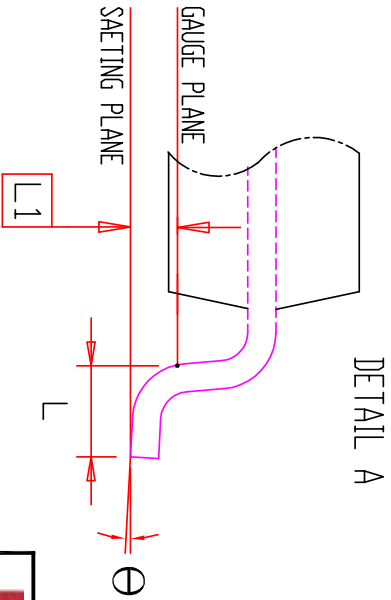
| Speed (ns) | Order Part No. | Package |
|------------|-------------------|--------------------------------|
| 10 | IS61LV256AL-10TI | TSOP - Type I |
| | IS61LV256AL-10TLI | TSOP - Type I, Lead-free |
| | IS61LV256AL-10JI | 300-mil Plastic SOJ |
| | IS61LV256AL-10JLI | 300-mil Plastic SOJ, Lead-free |



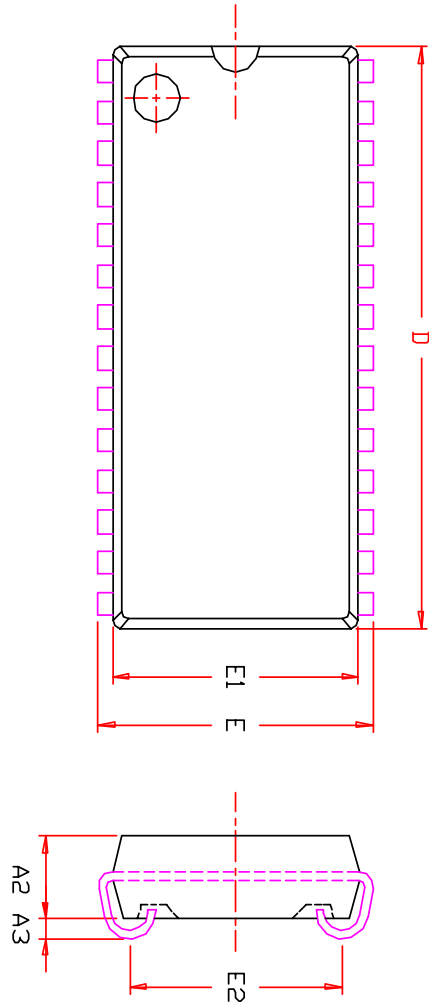
| SYMBOL | DIMENSION IN MM | | | DIMENSION IN INCH | | |
|--------|-----------------|-------|-------|-------------------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.95 | | 1.20 | 0.037 | | 0.049 |
| A1 | 0.05 | | 0.20 | 0.002 | | 0.008 |
| A2 | 0.90 | | 1.05 | 0.035 | | 0.041 |
| b | 0.17 | 0.22 | 0.27 | 0.006 | 0.009 | 0.011 |
| D | 13.20 | 13.40 | 13.60 | 0.520 | 0.528 | 0.535 |
| D1 | 11.70 | 11.80 | 11.90 | 0.461 | 0.465 | 0.469 |
| E | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 |
| e | 0.55 BSC. | | | 0.022 BSC. | | |
| L | 0.30 | 0.50 | 0.70 | 0.012 | 0.020 | 0.028 |
| L1 | 0.25 BSC. | | | 0.010 BSC. | | |
| ZD | 0.425 REF. | | | 0.017 REF. | | |
| Θ | 0 | 3° | 5° | 0 | 3° | 5° |

NOTE :

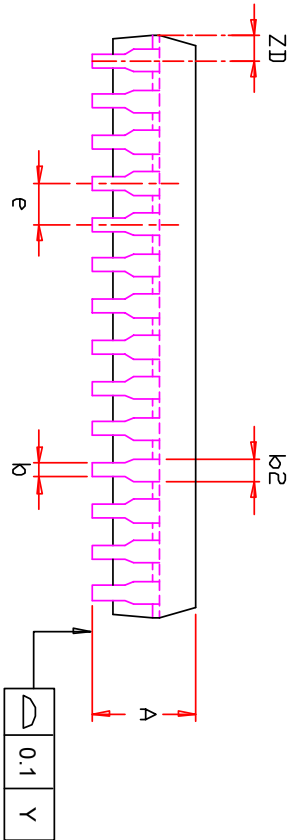
1. CONTROLLING DIMENSION : MM
2. DIMENSION D1 AND E DO NOT INCLUDE MOLD PROTRUSION.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION/INTRUSION.
4. Reference Document : JEDEC MO-183



| | | | |
|--|--|------|------------|
| | TITLE | REV. | DATE |
| | 28L 8x13.4mm TSOP-1 Package Outline | E | 04/22/2009 |



| SYMBOL | DIMENSION IN MM | | |
|--------|-----------------|------|-------|
| | MIN. | NOM. | MAX. |
| A | 3.05 | | 3.76 |
| A2 | 2.41 | 2.54 | 2.67 |
| A3 | 0.64 | | 1.09 |
| b | 0.36 | | 0.56 |
| b2 | 0.66 | | 0.81 |
| D | 17.70 | | 18.54 |
| E | 8.26 | 8.56 | 8.81 |
| E1 | 7.42 | | 7.75 |
| E2 | 6.22 | | 7.29 |
| e | 1.27 | BSC | |
| ZD | 0.95 | REF. | |
| Y | | 0.1 | |



- NOTE :**
1. Controlling dimension : mm
 2. Dimension D1 adn E do not include mold protrusion .
 3. Dimension b2 does not include dambar protrusion/intrusion.
 4. Formed leads shall be planar with respect to one another within 0.1mm at the seating plane after final test.

| | | | | | | |
|-------------|-----------------|-----------------------|-------------|----------|-------------|-------------------|
| ISSI | TITLE | 28L 300mil SOJ | REV. | C | DATE | 07/05/2006 |
| | Package Outline | | | | | |

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9